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FORM PTO-1449 (MODIFIED)					ATTY DOCKET N	SER	SERIAL NO.			
LIST OF PATENTS AND PUBLICATIONS					67,200-377			Filed Herewith		
FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT					APPLICANT Fu-Liang Yang					
(Use several sheets if necessary)					FILING DATE Filed Herewith					
REFERENCE D	ESIGNAT	ION U.S. F	ATENT DOCUM	ENT	S			,		
EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME			CLASS	SUB CLASS	FILING DATE	
OF	AA	5,023,671	Jun/1991	Di	Vincenzo et al					
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øF	AO	Sallagoity et al, "Analysis of Width Edge Effects in Advanced Isolation Schemes for Deep Submicron CMOS Technologies", IEEE Trans. on Electron Devices, 44(11), Nov. 1996, pp. 1900-05.								
08	AP	Matsuda et al, "Novel Corner Rounding Process for Shallow Trench Isolation Utilizing MSTS (Micro-Structure Transformation of silicon). IEEE IEDM98, pp. 137-40.								

EXAMINER DATE CONSIDERED 3/18/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.